

PATENTAtty Docket No.: 10018559-2
App. Ser. No.: 10/698,725**IN THE CLAIMS:**

Please find a listing of the claims below. The statuses of the claims are shown in parentheses.

1-12. (Cancelled)

13. (Original) A semiconductor device comprising:

a substrate having a substantially planar surface and an interior sloped surface;
a wettable layer adhered to a portion of the interior sloped surface; and
a solder layer adhered to a first portion of the wettable layer.

14. (Original) The semiconductor device of claim 13, wherein the wettable layer comprises a metal.

15. (Currently Amended) A semiconductor device comprising:

a substrate having a substantially planar surface and an interior sloped surface;
a wettable layer adhered to a portion of the interior sloped surface;
a solder layer adhered to a first portion of the wettable layer; and
The semiconductor device of claim 13, further comprising a coating layer adhered to a second portion of the wettable layer.

16. (Original) The semiconductor device of claim 15, wherein the coating layer is a non-wettable layer.

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17. (Original) The semiconductor device of claim 16, wherein the coating layer comprises a dielectric material.

18. (Original) The semiconductor device of claim 13, wherein the solder layer comprises a tin-bismuth compound.

19. (Original) The semiconductor device of claim 13, wherein the solder layer comprises a eutectic tin-lead compound.

20. (Currently Amended) A semiconductor device comprising:

a substrate having a substantially planar surface and an interior sloped surface;

a wettable layer adhered to a portion of the interior sloped surface;

a solder layer adhered to a first portion of the wettable layer; and

The semiconductor device of claim 13, further comprising a rigid organic film adhered to a portion of the substantially planar surface of the substrate and adjacent to a portion of the sloped surface.

21-28. (Cancelled)

29. (New) The semiconductor device of claim 13, wherein the wettable layer is adhered to a section of the substrate, further wherein the wettable layer extends from a first portion of the substantially planar surface to the portion of the interior sloped surface.

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30. (New) The semiconductor device of claim 13, wherein the length of the wettable layer is shorter than a length of the interior sloped surface.

31. (New) The semiconductor device of claim 15, wherein the wettable layer is adhered to a section of the substrate, further wherein the wettable layer extends from a first portion of the substantially planar surface to the portion of the interior sloped surface.

32. (New) The semiconductor device of claim 15, wherein the length of the wettable layer is shorter than a length of the interior sloped surface.

33. (New) The semiconductor device of claim 20, wherein the wettable layer is adhered to a section of the substrate, further wherein the wettable layer extends from a first portion of the substantially planar surface to the portion of the interior sloped surface.

34. (New) The semiconductor device of claim 20, wherein the length of the wettable layer is shorter than a length of the interior sloped surface.